Silicon NPN Power Transistors 2SD1291

DESCRIPTION

·With TO-3PN package
·Built-in damper diode
·High voltage ,high reliability
·Wide area of safe operation

APPLICATIONS

·For color TV horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

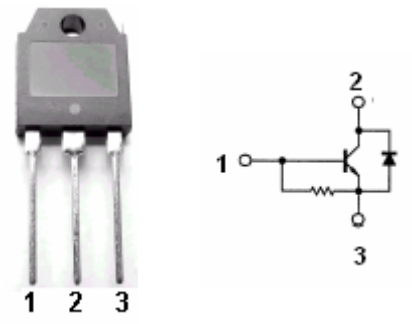


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current (DC)		3	A
I_{CM}	Collector current (Pulse)		13	A
P_C	Collector power dissipation	T_C=25□	65	W
T_j	Junction temperature		130	□
T_{stg}	Storage temperature		-55~130	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=500mA; I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=2.5A; I_B=0.8A			5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=2.5A; I_B=0.8A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=750V; I_E=0			50	μA
		V_{CB}=1500V; I_E=0			1	mA
h_{FE}	DC current gain	I_C=2.5A ; V_{CE}=10V	4		12	
t_s	Storage time	I_C=2.5A I_{Leak}=0.8A,L_B=5μH	4		8	μs
t_f	Fall time				1	μs
V_F	Diode forward voltage	I_F=-4A,I_B=0			2.2	V

PACKAGE OUTLINE

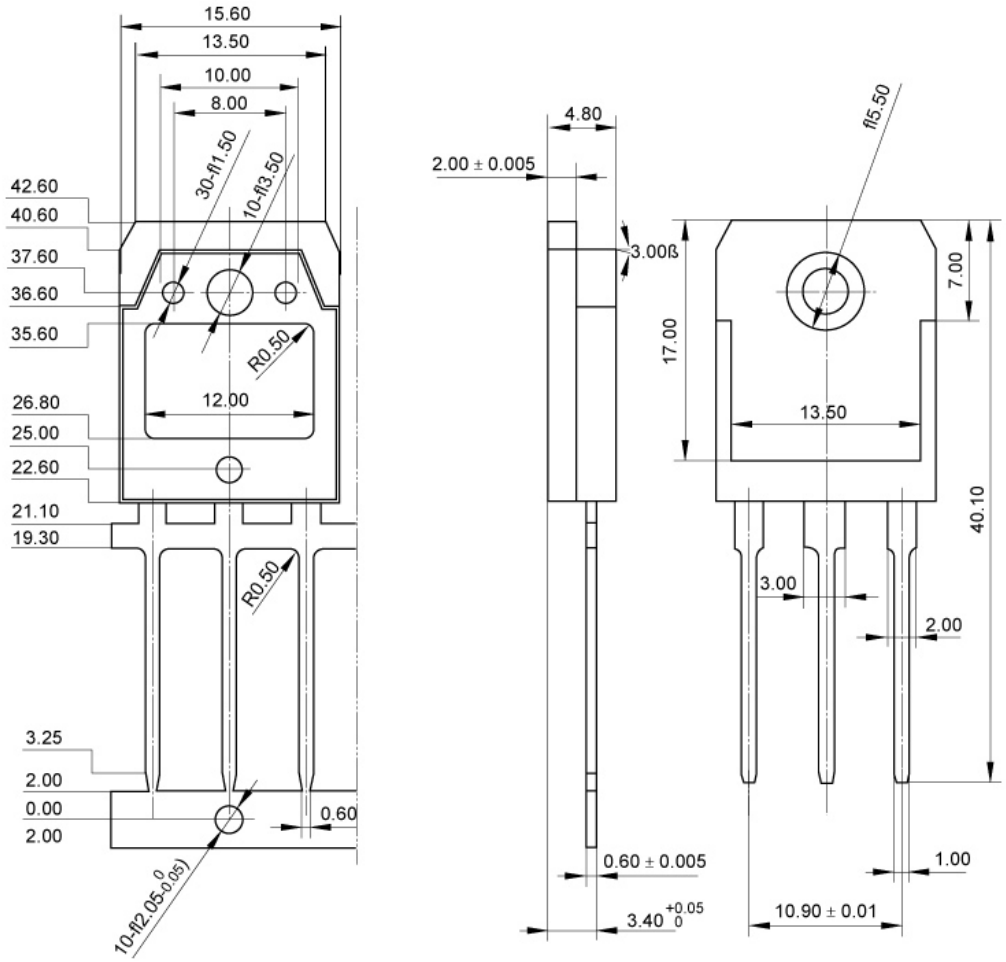


Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)